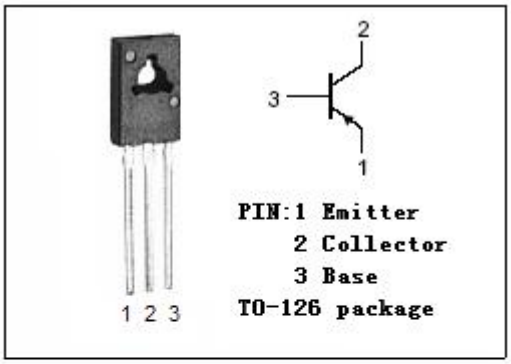
isc Silicon PNP Power Transistor — 2SB649

DESCRIPTION

- High Collector Current-I_C=-1.5A
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$=-120V(Min)
- Good Linearity of h_{FE}
- Low Saturation Voltage
- Complement to Type 2SD669
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

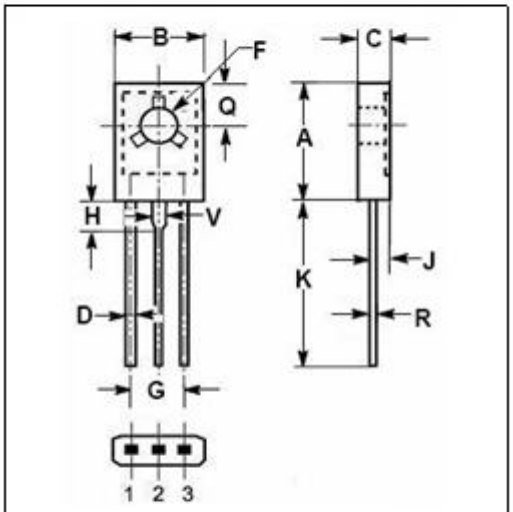


APPLICATIONS

- Power amplifier applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_{CP}	Collector Current-Pulse	-3	A
P_C	Collector Power Dissipation @ T_C=25℃	20	W
	Collector Power Dissipation @ T_a=25℃	1	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA ; I_E= 0	-180			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; R_{BE}= ∞	-120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Vltage	I_E= -1mA ; I_C=0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -150mA ; V_{CE}= -5V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -160V; I_E= 0			-10	μA
h_{FE-1}	DC Current Gain	I_C= -150mA ; V_{CE}= -5V	60		320	
h_{FE-2}	DC Current Gain	I_C=-500mA ; V_{CE}= -5V	30			

◆ **h_{FE-1} Classifications**

B	C	D
60-120	100-200	160-320